

# isc N-Channel MOSFET Transistor

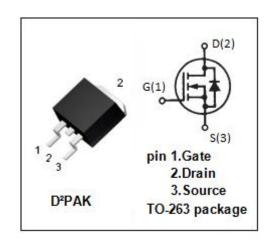
## IXTA8N50P

#### • FEATURES

- Static drain-source on-resistance:  $R_{DS}(on) \le 0.8\Omega@V_{GS}=10V$
- Fully characterized avalanche voltage and current
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

#### APPLICATION

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification



• ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>DSS</sub>	Drain-Source Voltage	500	V
V <sub>GS</sub>	Gate-Source Voltage	±30	V
Ι <sub>D</sub>	Drain Current-Continuous	8	А
I <sub>DM</sub>	Drain Current-Single Pulsed	14	А
P <sub>D</sub>	Total Dissipation @T <sub>C</sub> =25℃	150	W
Tj	Operating Junction Temperature	-55~150	$^{\circ}$
T <sub>stg</sub>	Storage Temperature	-55~150	$^{\circ}$

### • THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R <sub>th(j-c)</sub>	Junction-to-case thermal resistance	0.83	°C/W

	A B	K		- L	S
С	D		Q		U
	J H H		R	T.	w

	m	m
DIM	MIN	MAX
Α	10	
В	6.6	6.8
C	15.23	15.25
D	10.15	10.17
F G	0.76	0.78
G	1.26	1.28 1.6
Н	1.4	1.6
J	1.33	1.35
K	0.4	0.6
L	4.6	4.8
0	8.69	8.71
R	5.28	5.30
S	1.26	1.28
U	0.0	0.2
V	0.37	0.39
W	2.80	2.82



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#### **ELECTRICAL CHARACTERISTICS**

T<sub>C</sub>=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	МАХ	UNIT
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V; ID = 250 μ A	500		V
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> ; ID = 100 μ A	3.0	5.5	V
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> =10V; I <sub>D</sub> = 4A		0.8	Ω
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> = ±30V;V <sub>DS</sub> =0V		±100	nA
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> = V <sub>DSS</sub> ; V <sub>GS</sub> = 0V		5	- μΑ
		V <sub>DS</sub> = V <sub>DSS</sub> ; V <sub>GS</sub> = 0V;T <sub>J</sub> = 125°C		50	
V <sub>SD</sub>	Diode forward voltage	I <sub>F</sub> = 8A; V <sub>GS</sub> = 0V		1.5	V



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